Ordering number:EN4884

FX601

P-Channel Silicon MOSFET

Ultrahigh-Speed Switching Applications

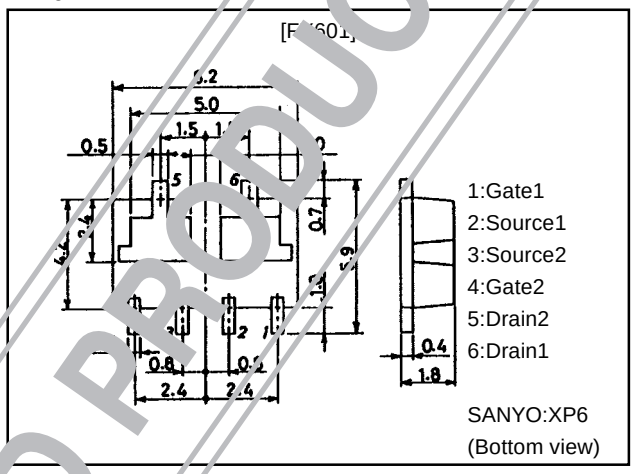
Features

- Composite type composed of tow low ON-resistance P-channel MOSFET chips for ultrahigh-speed switching and low-voltage drive.
- Facilitates high-density mounting.
- Tth FX601 is formed with two chips, each being equivalent to the 2SJ316, placed in one package.
- Matched pair characteristics.

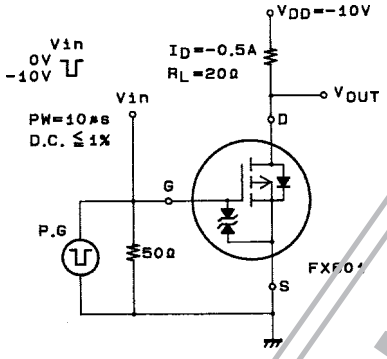
Package Dimensions

unit:mm

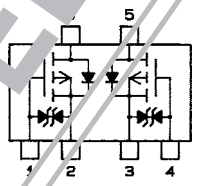
2120



Switching Time Test CIrcuit



Electrical Connection



1:Gate1
2:Source1
3:Source2
4:Gate2
5:Drain2
6:Drain1

(Top view)

Specifications

Absolute Maximum Ratings at T_a = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		–12	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Drain Current (DC)	I_D		–1	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	–4	A
Allowable Power Dissipation	P_D	Tc=25°C, 1unit	6	W
	P_D	Mounted on ceramic board (750mm²×0.8mm) 1unit	1.5	W
Total Dissipation	P_T	Mounted on ceramic board (750mm²×0.8mm)	2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		–55 to +150	°C

· Marking:601

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Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	I_D=–1mA, V_{GS}=0	–12			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=–12V, V_{GS}=0			–100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±12, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=–10V, I_D=–1mA	–1.0		–2.0	V
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS}=–10V, I_D=–500mA	0.8	1.2		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	I_D=–500mA, V_{GS}=–10V		0.3	0.42	Ω
	$R_{DS(on)}$	I_D=–500mA, V_{GS}=–4V		0.43	0.63	Ω
Input Capacitance	Ciss	V_{DS}=–10V, f=1MHz		170		pF
Output Capacitance	Coss	V_{DS}=–10V, f=1MHz		170		pF
Reverse Transfer Capacitance	Crss	V_{DS}=–10V, f=1MHz		40		pF
Turn-ON Delay Time	$t_{d(on)}$	See Specified Test Circuit		10		ns
Rise Time	t_r	See Specified Test Circuit		14		ns
Turn-OFF Delay Time	$t_{d(off)}$	See Specified Test Circuit		70		ns
Fall Time	t_f	See Specified Test Circuit		40		ns
Diode Forward Voltage	V_{SD}	I_S=–1A, V_{GS}=0		–0.9		V